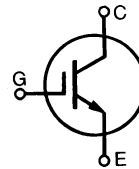


Low $V_{CE(sat)}$ IGBT High speed IGBT

IXGH/IXGM 17 N100
IXGH/IXGM 17 N100A

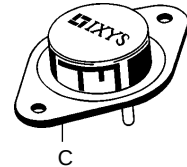
V_{CES}	I_{C25}	$V_{CE(sat)}$
1000 V	34 A	3.5 V
1000 V	34 A	4.0 V



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	1000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	34	A
I_{C90}	$T_C = 90^\circ\text{C}$	17	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	68	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 82\ \Omega$ Clamped inductive load, $L = 300\ \mu\text{H}$	$I_{CM} = 34$ @ $0.8\ V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	150	W
T_J		$-55 \dots +150$	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		$-55 \dots +150$	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10	Nm/lb.in.
Weight		TO-204 = 18 g, TO-247 = 6 g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD (IXGH)

TO-204 AE (IXGM)



G = Gate,
E = Emitter,

C = Collector,
TAB = Collector

Features

- International standard packages
- 2nd generation HDMOS™ process
- Low $V_{CE(sat)}$
 - for low on-state conduction losses
- High current handling capability
- MOS Gate turn-on
 - drive simplicity
- Voltage rating guaranteed at high temperature (125°C)

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

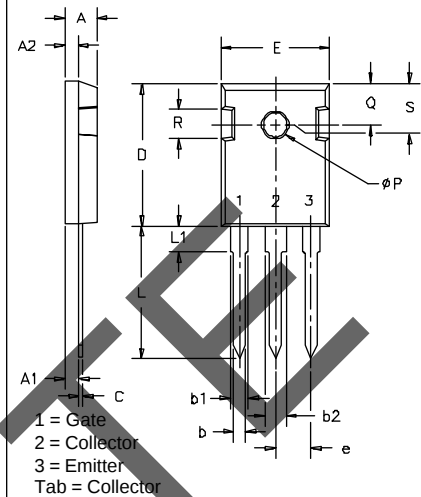
Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- High power density

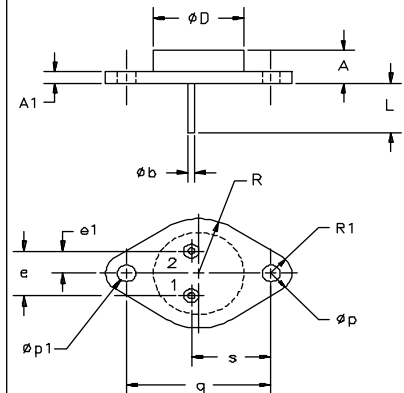
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 3\text{ mA}$, $V_{GE} = 0\text{ V}$	1000		V
$V_{GE(th)}$	$I_C = 250\ \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$			$250\ \mu\text{A}$ 1 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$			3.5 V 4.0 V
				17N100 17N100A

Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	I _C = I _{C90} ; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	6	15	S
C_{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		1500	pF
C_{oes}			175	pF
C_{res}			40	pF
Q_g	I _C = I _{C90} , V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		100	120 nC
Q_{ge}			20	30 nC
Q_{gc}			60	90 nC
t_{d(on)}	Inductive load, T_j = 25°C I _C = I _{C90} , V _{GE} = 15 V, L = 300 μH, V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 82 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _j or increased R _G		100	ns
t_{ri}			200	ns
t_{d(off)}			500	1000 ns
t_{fi}			750	ns
E_{off}			450	750 ns
			3	mJ
t_{d(on)}	Inductive load, T_j = 125°C I _C = I _{C90} , V _{GE} = 15 V, L = 300 μH V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 82 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _j or increased R _G		100	ns
t_{ri}			200	ns
E_{on}			2.5	mJ
t_{d(off)}			700	1000 ns
t_{fi}			1200	2000 ns
E_{off}			750	1000 ns
			8 6	mJ mJ
R_{thJC}				0.83 K/W
R_{thCK}			0.25	K/W

IXGH 17N100 and IXGH 17N100 A characteristic curves are located on the IXGH 17N100U1 and IXGH 17N100AU1 data sheets.

TO-247 AD Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.7	5.3
A1	.087	.102	2.2	2.54
A2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b1	.065	.084	1.65	2.13
b2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1		.177		4.50
φP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

TO-204AE Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.250	.450	6.4	11.4
A1	.060	.135	1.53	3.42
φb	.057	.063	1.45	1.60
φD		.875		22.22
e	.420	.440	10.67	11.17
e1	.205	.225	5.21	5.71
L	.440	.480	11.18	12.19
φp	.151	.165	3.84	4.19
φp1	.151	.165	3.84	4.19
q	1.187 BSC		30.15 BSC	
R	.495	.525	12.58	13.33
R1	.131	.188	3.33	4.77
s	.655	.675	16.64	17.14

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025